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Application Number	10/026 019
Filing Date	December 27, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02674 US

27	SEKIGUCHI, S., et al., "Long wavelength GaInAsP/InP laser with InGa contacts using AlAs/InP hole injecting tunnel junction", article, Japanese Journal of Applied Physics, Part 2, No 48, D4-15-1989, pgs L443-5.	
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	YANG, X., et al., "InGaAsN/GaAs quantum wells for 1.55 μ m lasers grown by molecular-beam epitaxy", article, Applied Physics Letters, Vol 78, No 26, pgs 4068-70. <i>NO DATA PROVIDED</i>	27
	YANG, M., et al., "Time-resolved reflection high energy electron diffraction analysis for atomic layer depositions of GaSb by molecular beam epitaxy", article, Journal of Crystal Growth, Vol 146, 1995, pgs 349-53.	
✓	YUEN, W., et al., "High-performance 1.5 μ m single-epitaxy top-emitting VCSEL", article, Electronics Letters, Vol 36, No 13, 06-22-2000, pgs 1121-3.	

Examiner Signature		Date Considered	07/04/04
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